MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

BSS138AKDW

Product specification





General Features

- 55V,0.3A, RDS(ON) =1.2Ω@VGS=10V
- Improved dv/dt capability
- Fast switching
- Green Device Available
- G-S ESD Protection Diode Embedded
- ESD protected up to 2KV

Reference News

Application

- Motor Drive
- Power Tools
- LED Lighting

PACKAGE OUTLINE	Pin Configuration	Marking
БОТ-363	D1 D2 G1 G2 G1 S1 S2	К38*** _{***} ЯЕ8



Absolute Maximum Ratings (TA=25 $^\circ\!\!\mathbb{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
Vds	Drain-Source Voltage	55	V
Vgs	Gate-Source Voltage	±20	V
le .	Drain Current – Continuous (T _A =250)	0.3	A
D	Drain Current – Continuous (T _A =70C)	0.2	А
Ідм	Drain Current – Pulsed ¹	0.9	A
D-	Power Dissipation (T _A =250)	0.28	W
Po	Power Dissipation – Derate above 250	0.002	W/ C
Тѕтс	Storage Temperature Range -50 to 150		С
TJ	Operating Junction Temperature Range	-50 to 150	С

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		450	C/ W

Electrical Characteristics (TJ=25 $^{\circ}\!\!\mathrm{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	Vgs=0V , Id=250uA	55			V
BV_dss/T_J	BVDss Temperature Coefficient	Reference to 250 , ID=1mA		0.04		V/ C
IDSS	Drain-Source Leakage Current	Vds=55V , Vgs=0V , Tj=250			1	uA
lgss	Gate-Source Leakage Current	Vgs= ±20V , Vds=0V			±10	uA



On Characteristics

RDS(ON)	Static Drain-Source On-Resistance	VGS=10V , ID=0.3A		1.2	1.5	Ω
NDO(ON)		VGS=4.5V , ID=0.2A		1.3	2.2	Ω
VGS(th)	Gate Threshold Voltage	VGS=VDS,ID =250uA	0.8	1.1	1.6	V
riangleVGS(th)	VGS(th) Temperature Coefficient	VGG-VDG, ID -2300A		-4		mV/ C
gfs	Forward Transconductance	VDS=10V , ID=0.1A		0.24		S

Dynamic and switching Characteristics

Qg	Total Gate Charge ^{2,3}		 1.1	
Qgs	Gate-Source Charge ^{2,3}	Vds=55V , Vgs=10V , Id=0.2A	 0.1	 nC
Qgd	Gate-Drain Charge ^{2,3}		 0.23	
Td(on)	Turn-On Delay Time ^{2,3}		 3	
Tr	$\label{eq:relation} \begin{array}{ c c c } \mbox{Rise Time}^{2,3} & \mbox{V}_{DD}\mbox{=}55\mbox{V},\mbox{V}_{GS}\mbox{=}10\mbox{V},\mbox{R}_{G}\mbox{=}6\mbox{\Omega} \end{array}$		 5	 ns
Td(off)	Turn-Off Delay Time ^{2,3}	ID=0.2A	 14	
Tf	Fall Time ^{2,3}		 9	
Ciss	Input Capacitance		 30.6	
Coss	Output Capacitance	Vos=10V , Vos=0V , F=1MHz	 5.5	 pF
Crss	Reverse Transfer Capacitance		 4	

Drain- Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current	Vg=V⊳=0V , Force Current			0.3	А
lsм	Pulsed Source Current				0.6	А
Vsd	Diode Forward Voltage	Vgs=0V , Is=1A , TJ=250			1.4	V

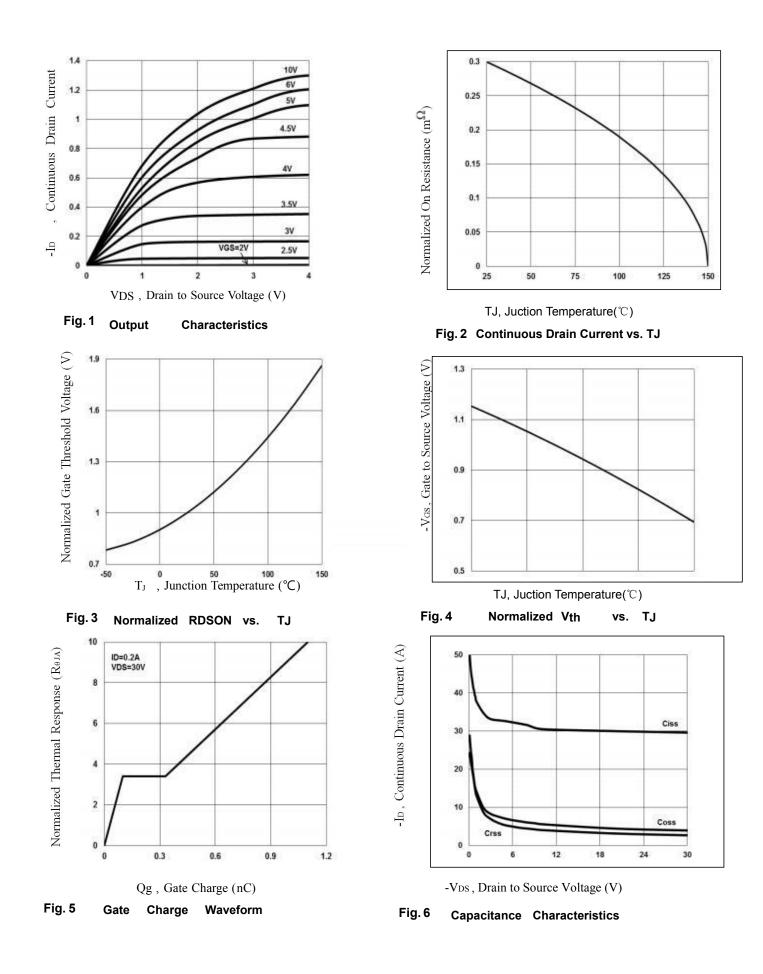
Note :

1 . Repetitive Rating : Pulsed width limited by maximum junction temperature.

2. The data tested by pulsed , pulse width $\ \leq \ 300\,\text{us}$, duty cycle $\ \leq \ 2\%$.

3. Essentially independent of operating temperature.







BSS138AKD

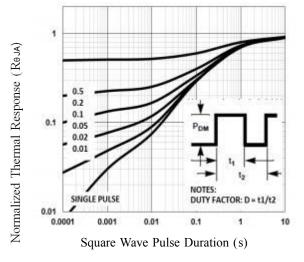
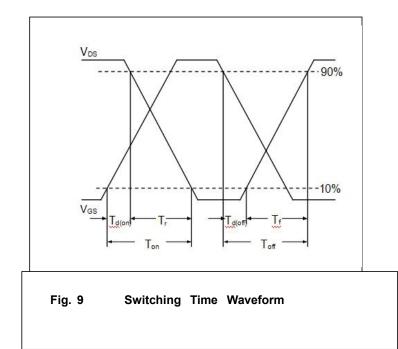
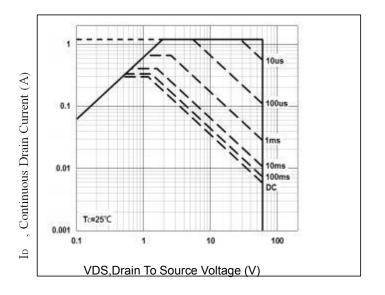


Fig. 7 Normalized Transient Impedance



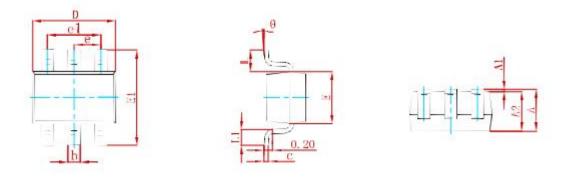






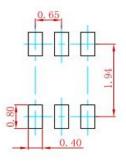


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions	In Inches	
Symbol	Min	Max	Min	Max	
А	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650) TYP	0.026	6 TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525	5 REF	0.021	REF	
L1	0.260	0.460	0.010	0.018	
9	0°	8°	0°	8°	

Suggested Pad Layout



Note: 1.Controlling dimension: In millimeters. 2.General tolerance: 0.05mm. 3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BSS138AKDW	SOT-363	3000



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